MOSFET - Power, Single N-Channel, TOLL

80 V, 0.79 mΩ, 457 A

NTBLS0D8N08X

$V_{(BR)DSS}$	$R_{DS(ON)}$ MAX	I_D MAX
80 V	0.79 mΩ @ 10 V	457 A

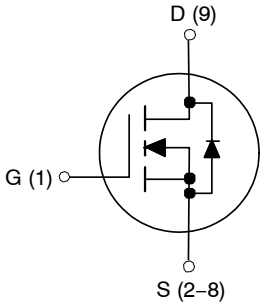
Features

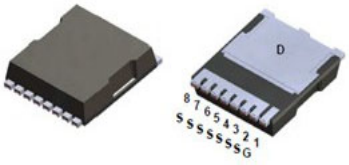
- Low Q_{RR}, Soft Recovery Body Diode
- Low $R_{DS(on)}$ to Minimize Conduction Losses
- Low Q_G and Capacitance to Minimize Driver Losses
- These Devices are Pb−Free, Halogen Free/BFR Free and are RoHS Compliant

Typical Applications

- Synchronous Rectification (SR) in DC−DC and AC−DC
- Primary Switch in Isolated DC−DC Converter
- Motor Drives

N−CHANNEL MOSFET





H−PSOF8L
CASE 100CU

MAXIMUM RATINGS (T_J = 25°C unless otherwise noted)

Parameter		Symbol	Value	Unit
Drain−to−Source Voltage		V_{DSS}	80	V
Gate−to−Source Voltage		V_{GS}	±20	V
Continuous Drain Current	T_C = 25°C	I_D	457	A
	T_C = 100°C		323	
Power Dissipation	T_C = 25°C	P_D	325	W
Pulsed Drain Current	T_C = 25°C, t_p = 100 μs	I_{DM}	1629	A
Pulsed Source Current (Body Diode)		I_{SM}	1629	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	−55 to +175	°C
Source Current (Body Diode)		I_S	547	A
Single Pulse Avalanche Energy (I_{PK} = 103 A)		E_{AS}	530	mJ
Lead Temperature for Soldering Purposes (1/8″ from case for 10 s)		T_L	260	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. The entire application environment impacts the thermal resistance values shown, they are not constants and are only valid for the particular conditions noted.
2. Actual continuous current will be limited by thermal & electromechanical application board design.
3. E_{AS} of 530 mJ is based on started T_J = 25°C, I_{AS} = 103 A, V_{DD} = 64 V, V_{GS} = 10 V, 100% avalanche tested.

MARKING DIAGRAM

A = Assembly Location
Y = Year
WW = Work Week
ZZ = Assembly Lot Code
0D8N08 = Specific Device Code

ORDERING INFORMATION

Device	Package	Shipping†
NTBLS0D8N08X	H−PSOF8L (Pb−Free)	2000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

Table 1. THERMAL CHARACTERISTICS

Parameter	Symbol	Value	Unit
Thermal Resistance, Junction−to−Case	$R_{\theta JC}$	0.46	°C/W
Thermal Resistance, Junction−to−Ambient	$R_{\theta JA}$	43	

Table 2. ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise noted)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Drain−to−Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS} = 0 V, I_D = 1 mA, T_J = 25°C	80			V
Drain−to−Source Breakdown Voltage Temperature Coefficient	$\Delta V_{(BR)DSS}/\Delta T_J$	I_D = 1 mA, Referenced to 25°C		35.5		mV/°C
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 80 V, T_J = 25°C			2	μA
		V_{DS} = 80 V, T_J = 125°C			250	
Gate−to−Source Leakage Current	I_{GSS}	V_{GS} = 20 V, V_{DS} = 0 V			100	nA
ON CHARACTERISTICS						
Drain−to−Source On Resistance	$R_{DS(on)}$	V_{GS} = 10 V, I_D = 80 A, T_J = 25°C		0.69	0.79	mΩ
		V_{GS} = 6 V, I_D = 71 A, T_J = 25°C		1	1.26	
Gate Threshold Voltage		V_{GS} = V_{DS}, I_D = 720 μA, T_J = 25°C	2.4		3.6	V
Gate Threshold Voltage Temperature Coefficient	$\Delta V_{GS(th)}/\Delta T_J$	V_{GS} = V_{DS}, I_D = 720 μA		−7.95		mV/°C
Forward Transconductance	g_{FS}	V_{DS} = 10 V, I_D = 80 A		485		S
CHARGES, CAPACITANCES & GATE RESISTANCE						
Input Capacitance	C_{iss}	V_{DS} = 40 V, V_{GS} = 0 V, f = 1 MHz		12920		pF
Output Capacitance	C_{oss}			3670		
Reverse Transfer Capacitance	C_{rss}			55		
Output Charge	Q_{oss}			262		nC
Total Gate Charge	$Q_{G(tot)}$	V_{DD} = 40 V, I_D = 80 A, V_{GS} = 6 V		109		
		V_{DD} = 40 V, I_D = 80 A, V_{GS} = 10 V		174		
Threshold Gate Charge	$Q_{G(th)}$			34		
Gate−to−Source Charge	Q_{gs}			54		
Gate−to−Drain Charge	Q_{gd}			32		
Gate Plateau Voltage	V_{gp}			4.6		V
Gate Resistance	R_g	f = 1 MHz		0.5		Ω
SWITCHING CHARACTERISTICS						
Turn−On Delay Time	$t_{d(on)}$	Resistive Load, V_{GS} = 0/10 V, V_{DD} = 40 V, I_D = 80 A, R_G = 2.5 Ω		34		ns
Rise Time	t_r			15		
Turn−Off Delay Time	$t_{d(off)}$			70		
Fall Time	t_f			20		
SOURCE−TO−DRAIN DIODE CHARACTERISTICS						
Forward Diode Voltage	V_{SD}	I_S = 80 A, V_{GS} = 0 V, T_J = 25°C		0.8		V
		I_S = 80 A, V_{GS} = 0 V, T_J = 125°C		0.66		
Reverse Recovery Time	t_{rr}	V_{GS} = 0 V, I_S = 80 A dI/dt = 1000 A/μs, V_{DD} = 40 V		48		ns
Charge Time	t_a			27		
Discharge Time	t_b			49		
Reverse Recovery Charge	Q_{rr}			464		nC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

TYPICAL CHARACTERISTICS

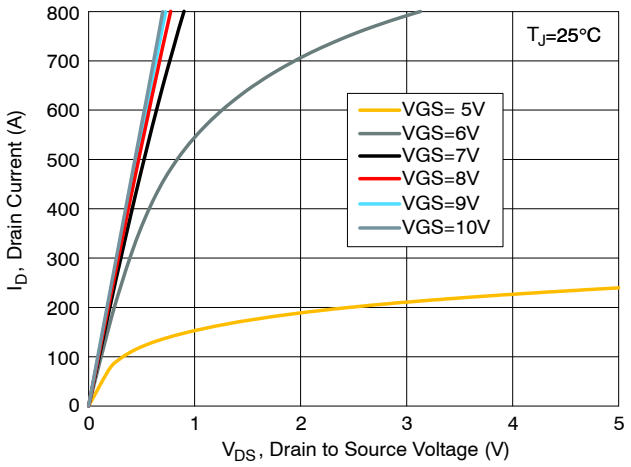


Figure 1. On−Region Characteristics

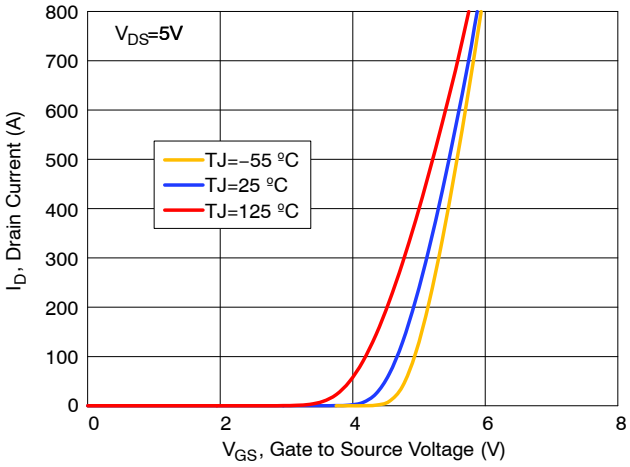


Figure 2. Transfer Characteristics

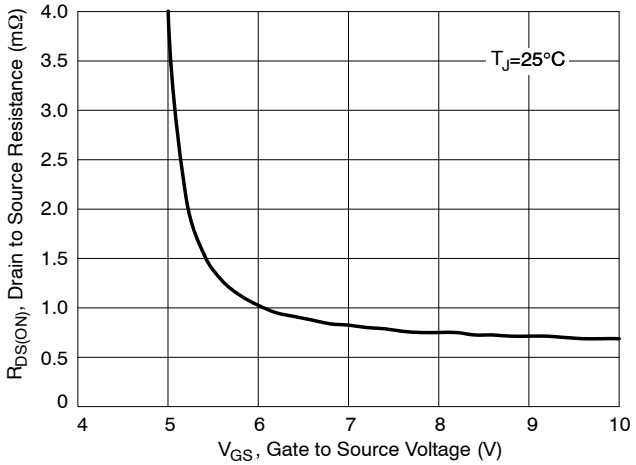


Figure 3. On−Resistance vs. Gate Voltage

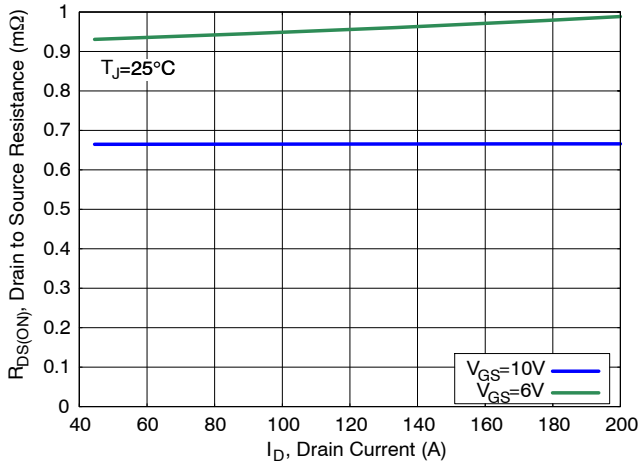


Figure 4. On−Resistance vs. Drain Current

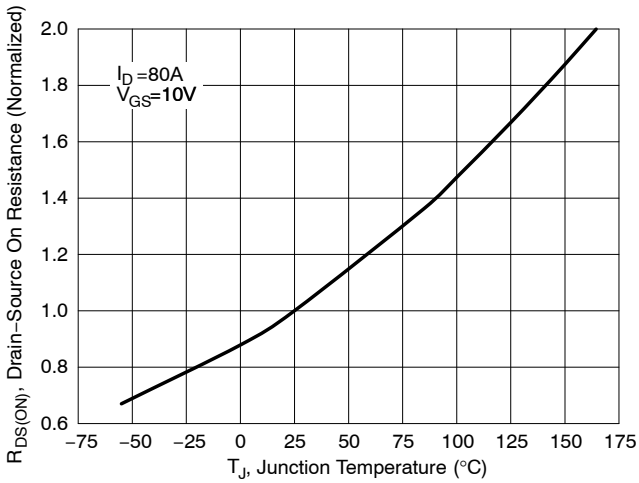


Figure 5. Normalized On−Resistance vs. Junction Temperature

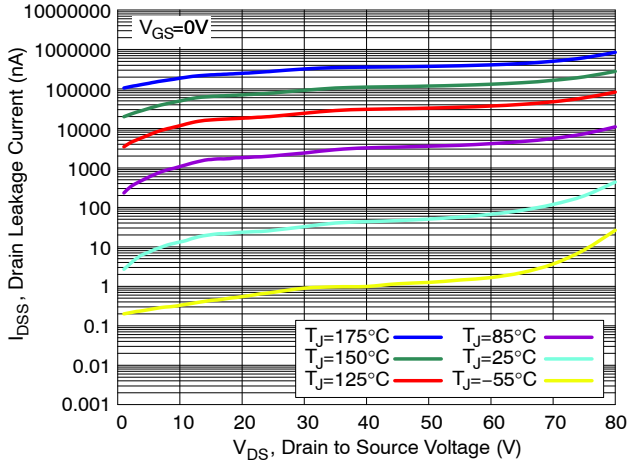


Figure 6. Drain Leakage Current vs. Drain Voltage

TYPICAL CHARACTERISTICS

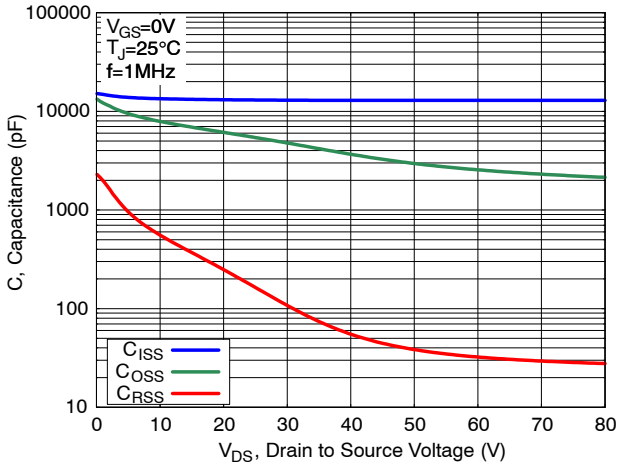


Figure 7. Capacitance Characteristics

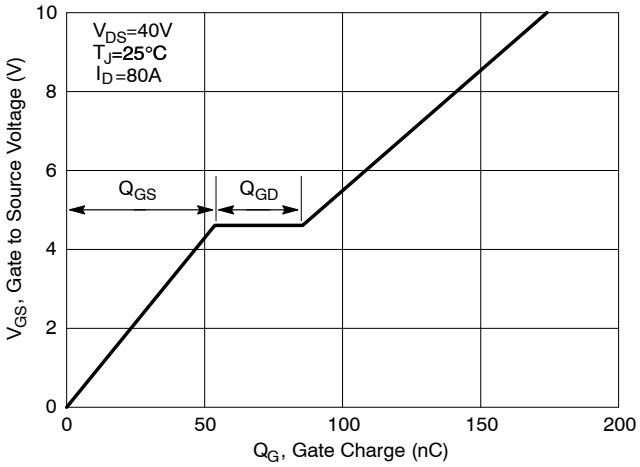


Figure 8. Gate Charge Characteristics

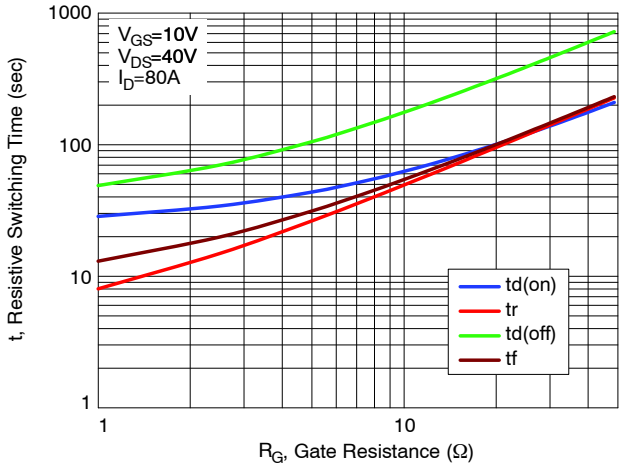


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

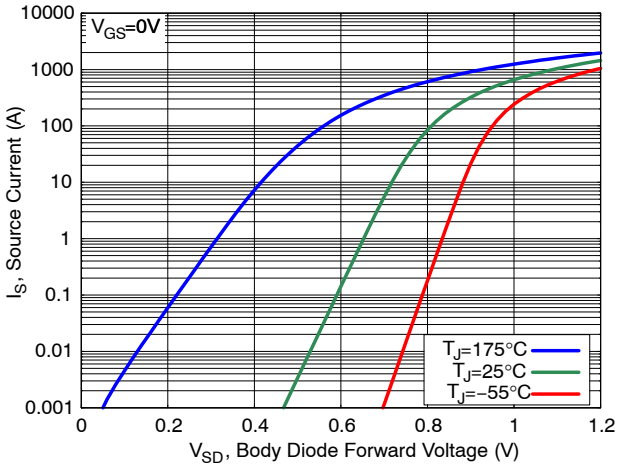


Figure 10. Diode Forward Characteristics

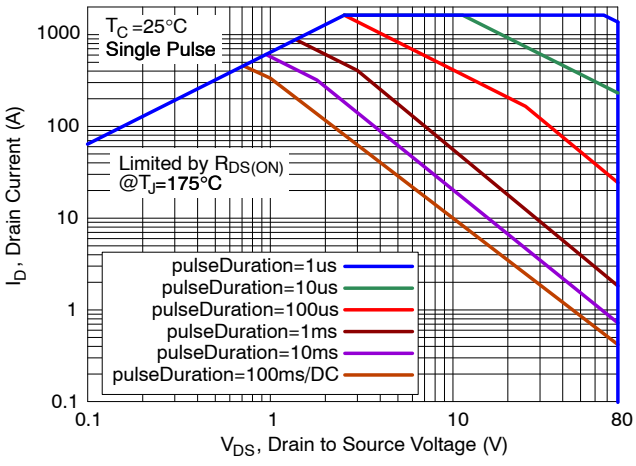


Figure 11. Safe Operating Area (SOA)

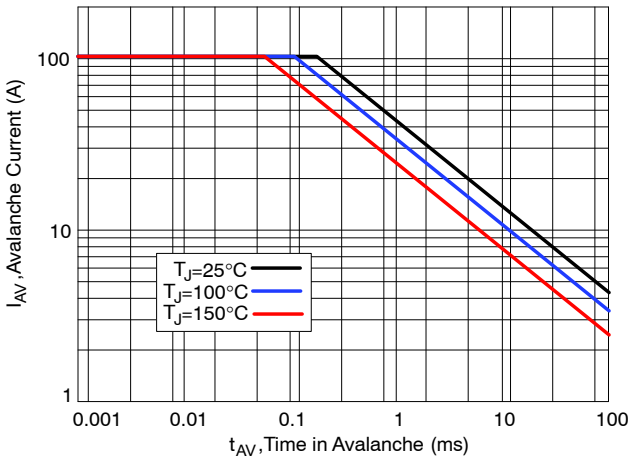


Figure 12. Avalanche Current vs. Pulse Time (UIS)

TYPICAL CHARACTERISTICS

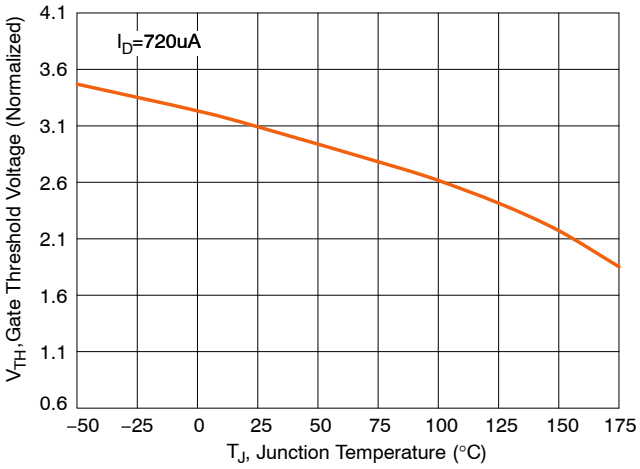


Figure 13. Gate Threshold Voltage vs. Junction Temperature

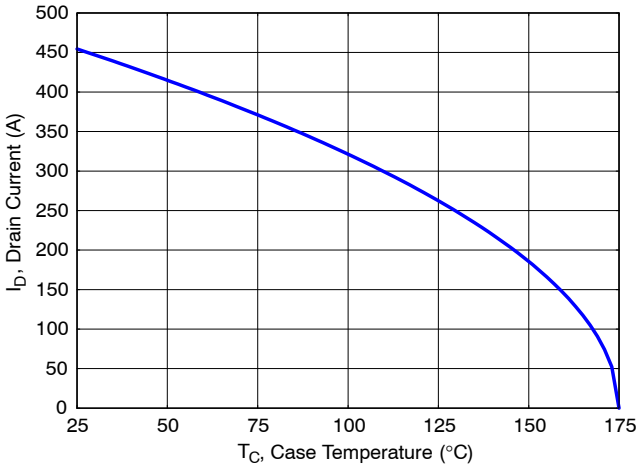


Figure 14. Maximum Current vs. Case Temperature

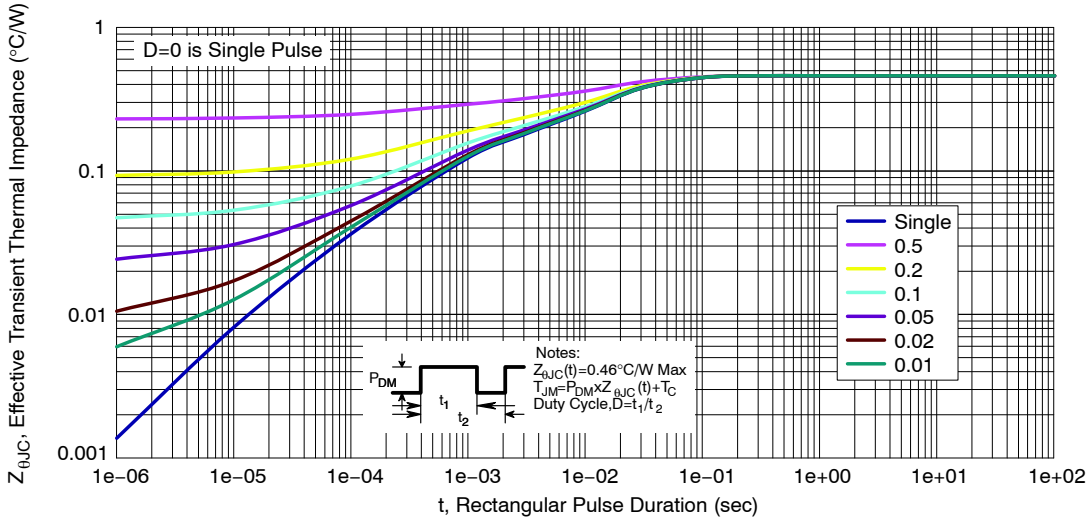
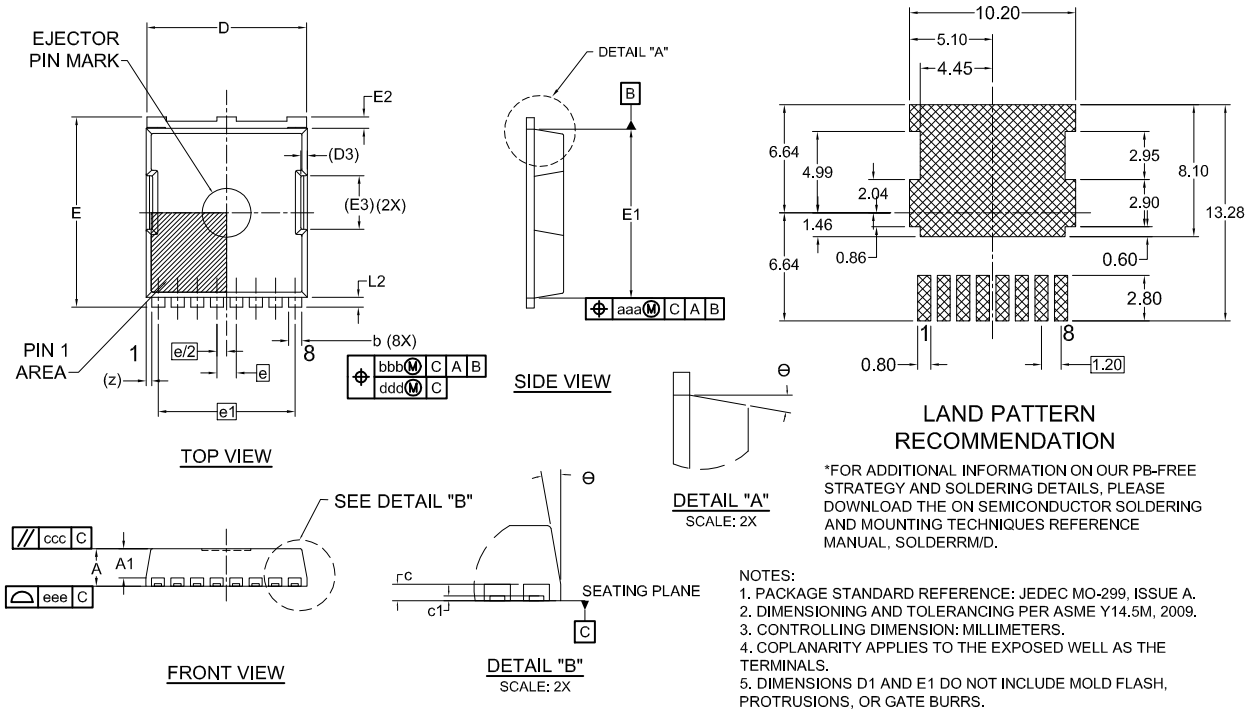
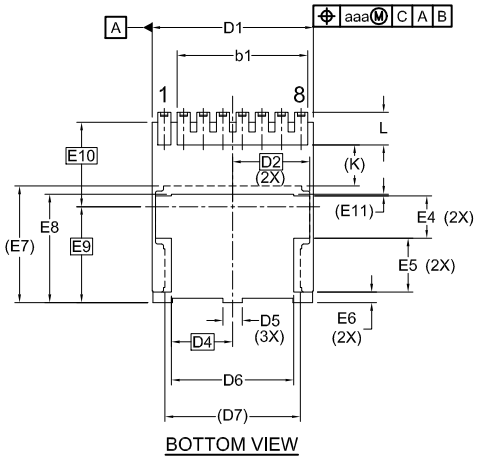


Figure 15. Transient Thermal Response

PACKAGE DIMENSIONS

H−PSOF8L 11.68x9.80
CASE 100CU
ISSUE B





NOTES:
1. PACKAGE STANDARD REFERENCE: JEDEC MO-299, ISSUE A.
2. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2009.
3. CONTROLLING DIMENSION: MILLIMETERS.
4. COPLANARITY APPLIES TO THE EXPOSED WELL AS THE TERMINALS.
5. DIMENSIONS D1 AND E1 DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.
6. SEATING PLANE IS DEFINED BY THE TERMINALS. "A1" IS DEFINED AS THE DISTANCE FROM THE SEATING PLANE TO THE LOWEST POINT ON THE PACKAGE BODY.

DIM	MILLIMETERS		
	MIN.	NOM.	MAX.
A	2.20	2.30	2.40
A1	1.70	1.80	1.90
b	0.70	0.80	0.90
b1		8.00 REF	
c	0.40	0.50	0.60
c1	0.10	---	--
D	9.70	9.80	9.90
D1	9.80	9.90	10.00
D2		4.73 BSC	
D3		0.40 REF	
D4		3.75 BSC	
D5	--	1.20	--
D6	7.40	7.50	7.60
D7		8.30 REF	
E	11.58	11.68	11.78
E1	10.28	10.38	10.48
E2	0.60	0.70	0.80
E3		3.30 REF	
E4	--	2.60	--
E5	--	3.30	--

DIM	MILLIMETERS		
	MIN.	NOM.	MAX.
E6	—	0.65	--
E7		7.15 REF	
E8	6.55	6.65	6.75
E9		5.89 BSC	
E10		5.19 BSC	
E11		0.10 REF	
e		1.20 BSC	
e/2		0.60 BSC	
e1		8.40 BSC	
K	2.43	2.53	2.63
L	1.90	2.00	2.10
L2	0.50	0.60	0.70
z		0.35 REF	
θ	0°	---	12°
aaa		0.20	
bbb		0.25	
ccc		0.20	
ddd		0.20	
eee		0.10	

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:
Email Requests to: orderlit@onsemi.com

onsemi Website: www.onsemi.com

TECHNICAL SUPPORT
North American Technical Support:
Voice Mail: 1 800−282−9855 Toll Free USA/Canada
Phone: 011 421 33 790 2910

Europe, Middle East and Africa Technical Support:
Phone: 00421 33 790 2910
For additional information, please contact your local Sales Representative

◊

X-ON Electronics

Largest Supplier of Electrical and Electronic Components

Click to view similar products for ON Semiconductor ***manufacturer:***

Other Similar products are found below :

BD442STU MC74LVX4245DWG MC78M05ACTG MC74LCX16244DTG KA7912ATU FQPF85N06 FQP4N80 MC78M15ACTG NLVVHC1G66DTT1G 2SA2012-TD-E MC74HC11ADTG FMBA14 NCP2823BFCT1G M74HCT4852ADTR2G MC34151P MC7818BTG MC78L08ACDG FDBL0150N80 FEBFL7733A_L53U021A MOC3042SM FPF2701MX FQD5N15TM FXLA104UM12X GF1B MUR3060WTG BS170_D74Z NCP1117DTAG NCV303LSN45T1G NCV551SN32T1G NDF04N60ZH NGTB10N60FG NL17SZ125DTT1G NLSX5014DR2G 1N5226B 1N5339B NSP8818MUTAG NTMFS6B05NT1G 1SMB5926BT3G 2SC3648T-TD-E ESD11N5.0ST5G FAN53600AUC33X FCP20N60 FDLL400 FDPC8016S FGH20N60SFDTU FGH40N60SFDTU SURA8220T3G FPF2124 FQD10N20CTM 2N5657G